

Initial Information Data Sheet

Inventor Information

Inventor One Given Name:: Toshiyuki
Family Name:: Okumura
Name Suffix::
Postal Address Line One:: 389-1-A201, Kaminosho-cho
Postal Address Line Two:: Nikaido,
City:: Tenri-shi
State or Province:: Nara
Postal or Zip Code:: 632-0087
Country:: JAPAN
Citizenship Country:: Japan

Correspondence Information

Name Line One:: Barry E. Bretschneider
Name Line Two:: Morrison & Foerster LLP
Address Line One:: 2000 Pennsylvania Ave., N.W.
Address Line Two::
City:: Washington
State or Province:: DC
Country:: USA
Postal or Zip Code:: 20006-1888
Telephone:: 202-887-1500
Fax:: 202-263-8396
Electronic Mail:: BBretschneider@mofo.com

Application Information

Title Line One:: Gallium Nitride Semiconductor Light
Title Line Two:: Emitting Device Having Multi-Quantum
Title Line Three:: -Well Structure Active Layer, And
Title Line Four:: Semiconductor Laser Light Source Device
Total Drawing Sheets:: 10
Formal Drawings?:: Yes
Application Type:: Utility
Docket Number:: 204552016410

Representative Information

Representative Customer Number:: 25227

Continuity Information

This application is a::

> Application One::

Filing Date::

Continuation of

09/380,537

September 2, 1999

which is a::

>>Application Two::

Filing Date::

371 of

PCT/JP98/00828

February 27, 1998

Prior Foreign Applications

Foreign Application One::

Filing Date::

Country::

Priority Claimed::

JP 9-52596

March 7, 1997

Japan

Yes

Foreign Application Two::

Filing Date::

Country::

Priority Claimed::

JP 9-65725

March 19, 1997

Japan

Yes